

SOT89 NPN SILICON POWER (SWITCHING) TRANSISTOR

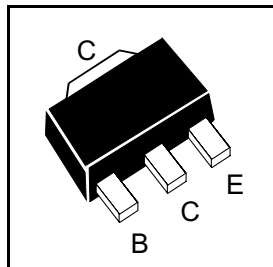
ISSUE 1 - DECEMBER 1998

FCX1051A

FEATURES

- * **2W POWER DISSIPATION**
- * 10A Peak Pulse Current
- * Excellent H_{FE} Characteristics up to 10 Amps
- * Extremely Low Saturation Voltage E.g. 17mv Typ.
- * Extremely Low Equivalent On-resistance;
 $R_{CE(sat)}$ 57m Ω at 3A

Complimentary Type - FCX1151A
Partmarking Detail - 051



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current **	I_{CM}	10	A
Continuous Collector Current	I_C	3	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1 † 2 ‡	W W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

† recommended P_{tot} calculated using FR4 measuring 15x15x0.6mm

‡ Maximum power dissipation is calculated assuming that the device is mounted on FR4 substrate measuring 40x40x0.6mm and using comparable measurement methods adopted by other suppliers.

**Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle \leq 2%

Spice parameter data is available upon request for these devices.

Refer to the handling instructions for soldering surface mount components.

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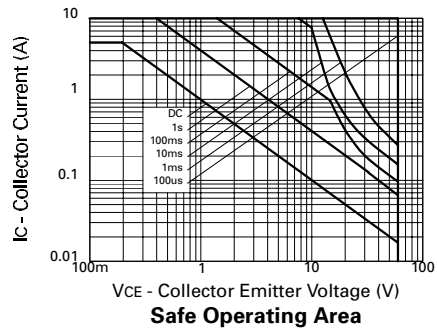
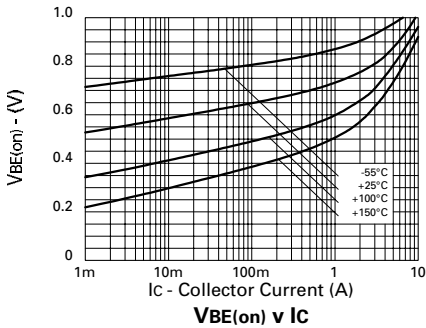
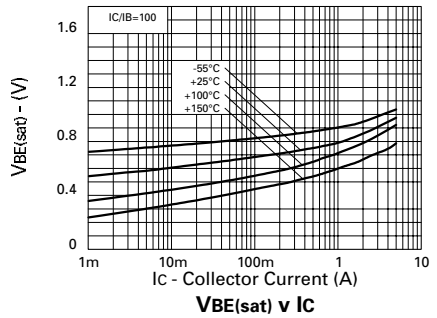
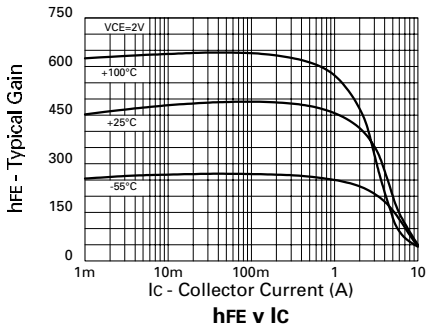
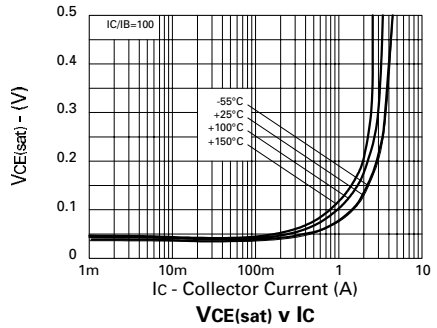
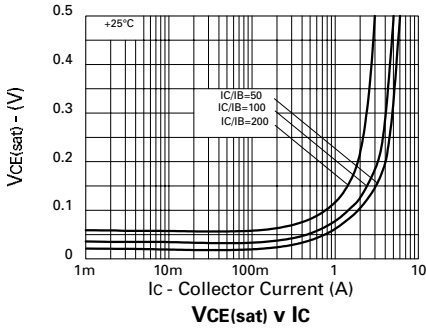
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	Min	Typ	Max	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	150			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CES}	150			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CEO}	40			V	$I_C=10\text{mA}$
Collector-Emitter Breakdown Voltage	V_{CEV}	150			V	$I_C=100\mu\text{A}, V_{EB}=1\text{V}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		0.3	10	nA	$V_{CB}=120\text{V}$
Emitter Cut-Off Current	I_{EBO}		0.3	10	nA	$V_{EB}=4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}		0.3	10	nA	$V_{CES}=120\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		17 85 140 170 250	25 120 180 250 340	mV	$I_C=0.2\text{A}, I_B=10\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=2\text{A}, I_B=20\text{mA}^*$ $I_C=3\text{A}, I_B=40\text{mA}^*$ $I_C=5\text{A}, I_B=100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		880	1000	mV	$I_C=3\text{A}, I_B=40\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		840	950	mV	$I_C=3\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	290 270 270 130 40	440 450 360 220 55	1200		$I_C=10\text{mA}, V_{CE}=2\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$ $I_C=3\text{A}, V_{CE}=2\text{V}^*$ $I_C=5\text{A}, V_{CE}=2\text{V}^*$ $I_C=10\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T		155		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		27	40	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	t_{on}		220		ns	$I_C=3\text{A}, I_B=30\text{mA}, V_{CC}=10\text{V}$
	t_{off}		540		ns	$I_C=3\text{A}, I_B=30\text{mA}, V_{CC}=10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS





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